PATENT

Attorney Docket No.: SAM-0313

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Soo-geun Lee, et al. Examiner: Nguyen, H. Serial No.: 10/081,661 Group Art Unit: 2812 Filing Date: February 22, 2002 METHOD OF MANUFACTURING INTERCONNECTION LINE IN Title: SEMICONDUCTOR DEVICE CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8 I hereby certify that this correspondence is being deposited with the United States Post Office as First Class Mail on the date indicated below in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT Sir: This Information Disclosure Statement is submitted: 01/22/2004 DTESSEM1 00000086 10081661 under 37 CFR 1.129(a), or 01 FC:1806 180.00 DP (First/Second submission after Final Rejection) [ ] under 37 CFR 1.97(b), or (Within three months of filing national application other than a CPA under §1.53(d); or within three months of date of entry of the national stage in international application; or before mailing date of first Office Action on the merits; or before mailing date of first Office Action after filing RCE under §1.114, whichever occurs last) under 37 CFR 1.97(c) together with either: [X] [ ] a Statement under 37 CFR 1.97(e), as checked below, or the \$180.00 fee under 37 CFR 1.17(p), or [X](After the 37 CFR 1.97(b) time period, but before final action or notice of allowance, or other action which closes prosecution, whichever occurs first) under 37 CFR 1.97(d) together with:

(Filed after final action or notice of allowance, whichever occurs first, but before

a Statement under 37 CFR 1.97(e), as checked below, and

the \$180.00 fee set forth in 37 CFR 1.17(p).

payment of the issue fee)

[ ]

Applicant(s): Soo-geun Lee, et al.

Serial No.:

[]

[]

[]

abstract.

10/081,661

## Statement Under 37 1 97(e)

		Statement Onder 37 1.57(c)				
	[]	Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.				
	[]	No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, after making reasonable inquiry, was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.				
Enclo	sed herewith is	form PTO-1449:				
[X]	Copies of cited references are enclosed.					
[]	Copies of cited references are enclosed except those entered in prior application, U.S. Serial No, and references that are not required to be submitted under 37 CFR 1.98.					
[]	The listed references were cited in a counterpart foreign application.					
Conci	se Explanation	Requirement (non-English references):				
[ ] satisfi	The "concise ed by:	explanation" requirement under 36 CFR 1.98(a)(3)(i) for reference XX is				
•	[] the ex	planation provided on the attached sheet.				

It is requested the information disclosed herein be made of record in this application.

the explanation provided in the Specification.

Serial No.: 10/081,661

Method of payment:

[X] Enclosed is a check in the amount of \$180.00

[] Please charge Deposit Account of 50-1798 in the amount of \_\_\_\_\_\_.

[] Two duplicate copies of this Statement are enclosed.

[X] Please charge any deficiency in fees and credit any overpayment to Deposit Account No. 50-1798.

Respectfully submitted,

Registration Number 36,610 Attorney for Applicants

Date: January 15, 2 Mills & Onello, ALP

Eleven Beacon Street, Suite 605 Boston, Massachusetts 02108

Applicant(s): Soo-geun Lee, et al.

Telephone: (617) 994-4900 Facsimile: (617) 742-7774

J:\SAM\0313\suppidsform.wpd

Sheet 1 of 1

bubst. Form PTO-1449

## NFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

SAM-0313 Application Number 10/081,661
Applicant

Soo-geun Lee, et al.

Filing Date Group Art Unit
2-22-02 2812

			<del></del>						
		<u>,</u>	U. S. P	atent Documents	<del></del>	· · · · · · · · · · · · · · · · · · ·			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS		DATE OPRIATE	
	AA								
	AB	6,559,520	5/6/03	Matsuki, et al.	257	642	4/25/02		
	AC	6,514,880	2/4/03	Matsuki, et al.	438	780	4/6/01		
_	AD	6,455,445	9/24/02	Matsuki	438	789	3/28/01		
	AE	6,432,846	8/13/02	Matsuki	438	790	10/18/00		
	AF	6,410,463	6/25/02	Matsuki	438	790	10/18/00		
	AG	6,383,955	5/7/02	Matsuki, et al.	438	790	6/7/99		
	AH	6,352,945	3/5/02	Matsuki, et al.	438	778	6/7/99		
	Al	6,057,239	5/2/00	Wang, et al.	438	689	12/17/97		
	AJ	01/0046778	11/29/01	Wang, et al.	H01L	21/302	3/22/00		
	AK								
		F	DREIGN F	PATENT DOCUMEN	TS				
		DOCUMENT NUMBER	DATE	COUNTRY.	CLASS	SUBCLASS	Translation YES NO		
	AL								
	AM								
	AN								
	AO			•					
- 11 11 11 11	AP								
	AQ								
	OTHE	R DOCUMEN	ITS ( <i>Inclu</i>	iding Author, Title,	Date, P	ertinent	Pages	, Etc	
		Jiang, P., et al., "Trench Etch Processes for Dual Damascene Patterning of Low-k Dielectrics, J. Vac. Sci. Technology, A 19(4), Jul/Aug 2001, p. 1388-1391.							
	AR	Jiang, P., et a Dielectrics, J.	I., "Trench Vac. Sci. T	Etch Processes for Dual echnology, A 19(4), Jul/	Damasce Aug 2001	ne Pattern , p. 1388-	ing of t 1391.	.ow- <i>k</i>	
	AR	Jiang, P., et a Dielectrics, J.	I., "Trench Vac. Sci. T	Etch Processes for Dual echnology, A 19(4), Jul/	Damasce Aug 2001	ne Pattern , p. 1388-	1391.	.ow- <i>k</i>	
	ļ	Jiang, P., et a Dielectrics, J.	I., "Trench Vac. Sci. T	Etch Processes for Dual echnology, A 19(4), Jul/	Damasce Aug 2001	ne Pattern , p. 1388-	1391.	.ow-k	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy with next communication to applicant.

L&K Subst. PTO-1449 (1-94)